

HiPerFET™ Power MOSFETs IXFK 27N80

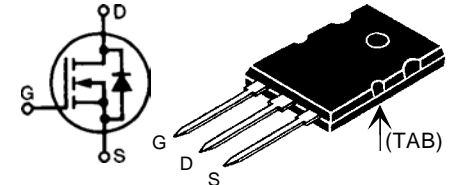
N-Channel Enhancement Mode
Avalanche Rated, High dv/dt, Low t_{rr}

IXFK 25N80
IXFN 27N80
IXFN 25N80

V_{DSS}	I_{D25}	$R_{DS(on)}$
800 V	27 A	0.30 Ω
800 V	25 A	0.35 Ω
800 V	27 A	0.30 Ω
800 V	25 A	0.35 Ω

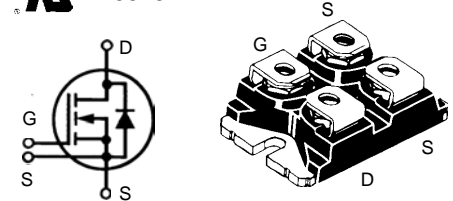
Symbol	Test Conditions	Maximum Ratings		
		IXFK	IXFN	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	800	800	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1\text{ M}\Omega$	800	800	V
V_{GS}	Continuous	± 20	± 20	V
V_{GSM}	Transient	± 30	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$, Chip capability	27N80	27	A
		25N80	25	A
		IXFK 27N80	108	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	25N80	100	A
		IXFK 27N80	14	A
I_{AR}	$T_C = 25^\circ\text{C}$	25N80	13	A
		IXFK 27N80	13	A
E_{AR}	$T_C = 25^\circ\text{C}$	30	30	mJ
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2\ \Omega$	5	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	500	520	W
T_J		-55 ... +150		$^\circ\text{C}$
T_{JM}		150		$^\circ\text{C}$
T_{stg}		-55 ... +150		$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	300	-	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS	-	2500	V~
	$I_{ISOL} \leq 1\text{ mA}$	-	3000	V~
M_d	Mounting torque	0.9/6	1.5/13	Nm/lb.in.
	Terminal connection torque	-	1.5/13	Nm/lb.in.
Weight		10	30	g

TO-264 AA (IXFK)



miniBLOC, SOT-227 B (IXFN)

E153432



G = Gate
S = Source
D = Drain
TAB = Drain
Either Source terminal at miniBLOC can be used as Main or Kelvin Source

Features

- International standard packages
- JEDEC TO-264 AA, epoxy meet UL 94 V-0, flammability classification
- miniBLOC, with Aluminium nitride isolation
- Low $R_{DS(on)}$ HDMOST™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- Temperature and lighting controls

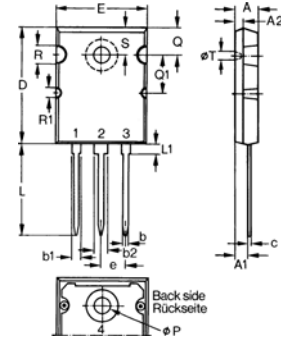
Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0\text{ V}$, $I_D = 3\text{ mA}$ V_{DSS} temperature coefficient	800	0.096	V %/K
$V_{GH(th)}$	$V_{DS} = V_{GS}$, $I_D = 8\text{ mA}$ $V_{GS(th)}$ temperature coefficient	2	-0.214	V %/K
I_{GSS}	$V_{GS} = \pm 20\text{ V}_{DC}$, $V_{DS} = 0$			$\pm 200\text{ nA}$
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$, $T_J = 25^\circ\text{C}$ $V_{GS} = 0\text{ V}$, $T_J = 125^\circ\text{C}$			500 μA 2 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			25N80 0.35 Ω 27N80 0.30 Ω

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	16	28	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$	7930	8400	9740
C_{oss}		630	712	790
C_{rss}		146	192	240
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1\ \Omega$ (External),		30	ns
t_r			80	ns
$t_{d(off)}$			75	ns
t_f			40	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$	320	350	400
Q_{gs}		38	46	56
Q_{gd}		120	130	142
R_{thJC}	TO-264 AA		0.15	0.25
R_{thCK}	TO-264 AA		0.15	K/W
R_{thJC}	miniBLOC, SOT-227 B		0.05	0.24
R_{thCK}	miniBLOC, SOT-227 B		0.05	K/W

TO-264 AA Outline

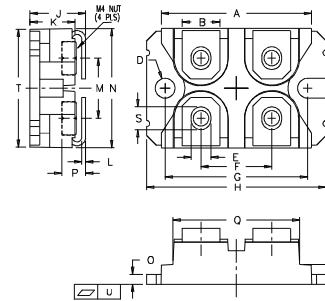


Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46BSC		.215BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$	27N80 25N80		27 25
I_{SM}	Repetitive; pulse width limited by T_{JM}	27N80 25N80		108 100
V_{SD}	$I_F = 100\text{ A}, V_{GS} = 0\text{ V},$ Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5
t_{rr}	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		250 400
Q_{RM}		$T_J = 25^\circ\text{C}$	2	ns
I_{RM}			17	μC A

miniBLOC, SOT-227 B



M4 screws (4x) supplied

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	38.00	38.23	1.496	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.76	0.84	0.030	0.033
M	12.60	12.85	0.496	0.506
N	25.15	25.42	0.990	1.001
O	1.98	2.13	0.078	0.084
P	4.95	5.97	0.195	0.235
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.174
S	4.72	4.85	0.186	0.191
T	24.59	25.07	0.968	0.987
U	-0.05	0.1	-0.002	0.004

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	

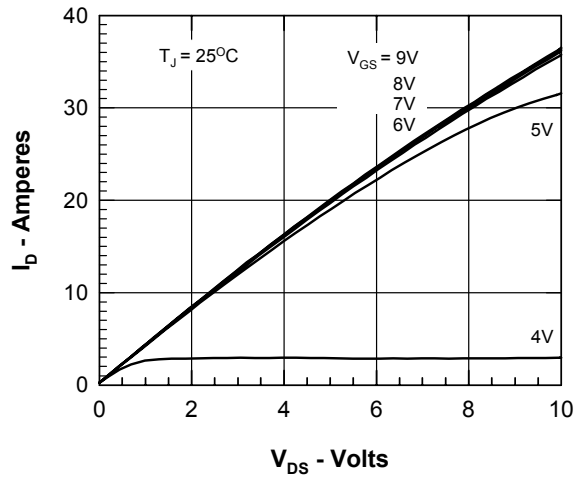


Figure 1. Output Characteristics at 25°C

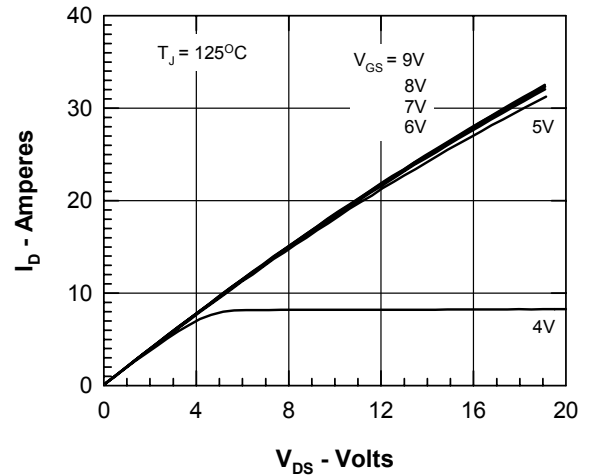


Figure 2. Output Characteristics at 125°C

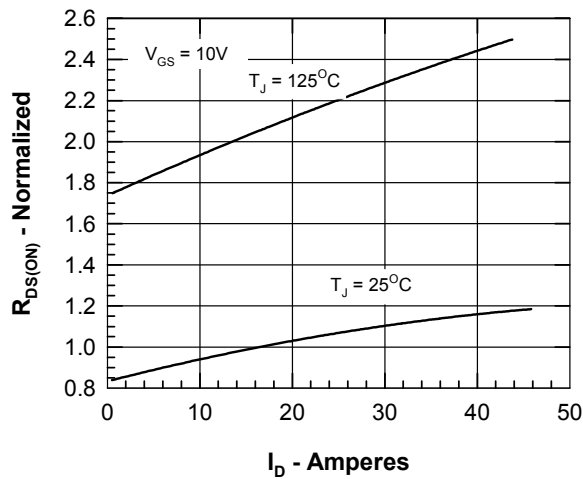
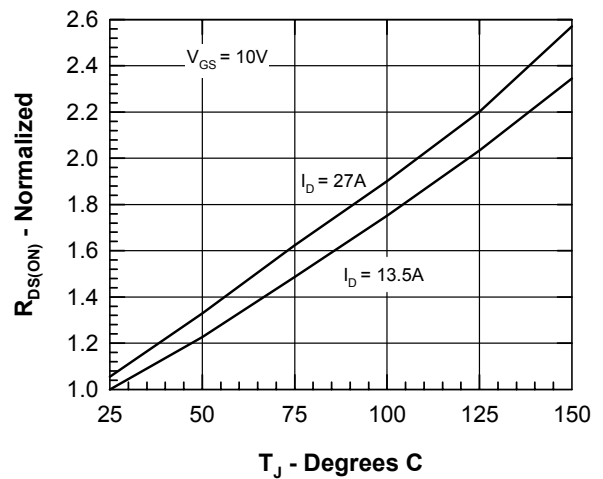
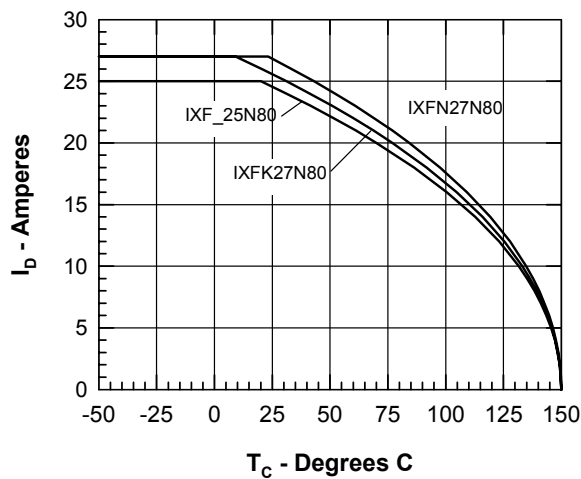

 Figure 3. $R_{DS(on)}$ normalized to $0.5 I_{D25}$ value vs. I_D

 Figure 4. $R_{DS(on)}$ normalized to $0.5 I_{D25}$ value vs. T_J


Figure 5. Drain Current vs. Case Temperature

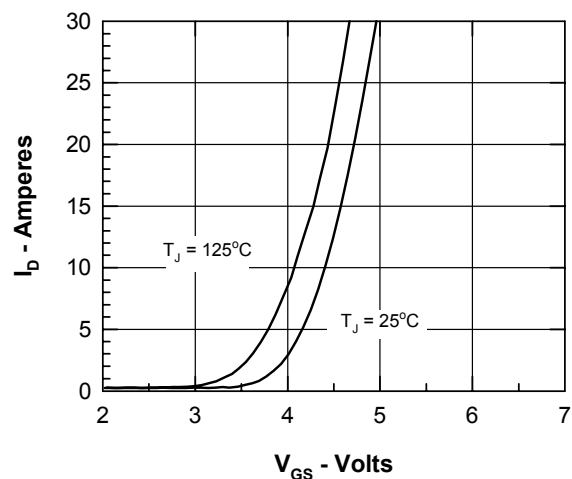


Figure 6. Admittance Curves

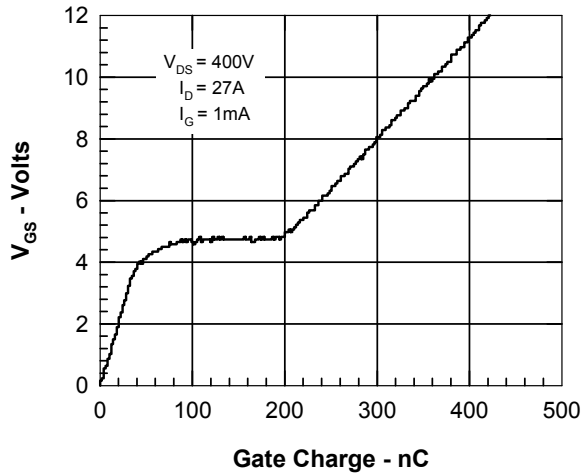


Figure 7. Gate Charge

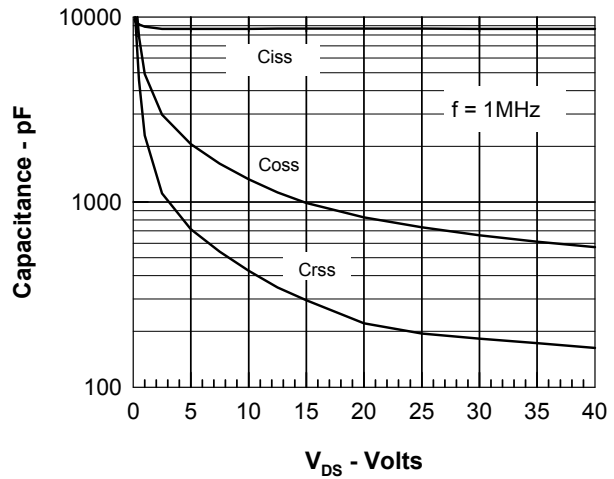


Figure 8. Capacitance Curves

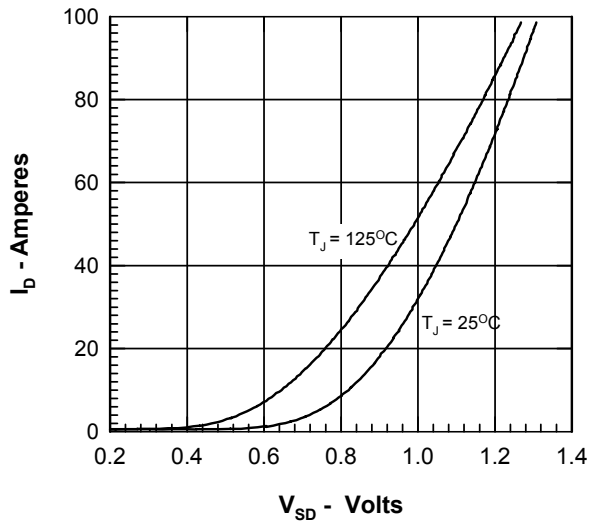


Figure 9. Forward Voltage Drop of the Intrinsic Diode

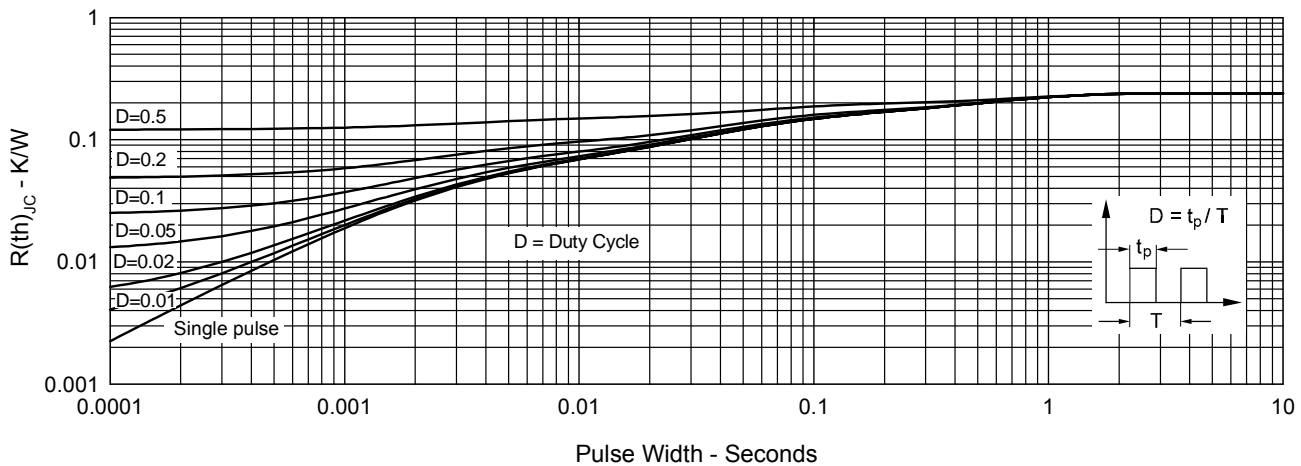


Figure 10. Transient Thermal Resistance

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